

Features

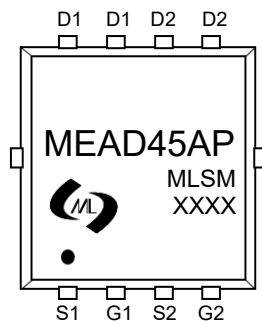
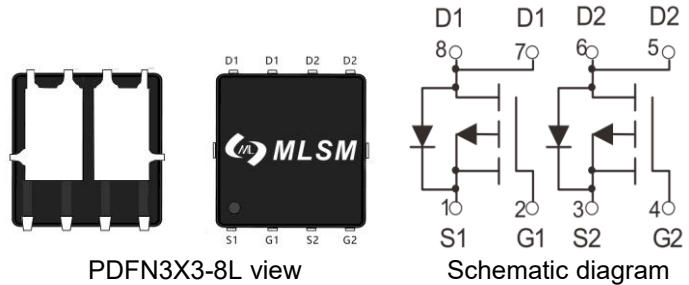
- High density cell design for ultra low RDS(ON)
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high EAS

Product Summary

V_{DS}	$R_{DS(ON)}$ TYP	I_D
-30V	8.0mΩ@-10V	-45A
	12mΩ@-4.5V	

Application

- Battery and loading switching
- Excellent package for good heat dissipation



MEAD45AP : Device code
 XXXX : Code

Marking and pin assignment



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V_{DS}	Drain-Source Breakdown Voltage	-30	V
V_{GS}	Gate-Source Voltage	±20	V
E_{AS}	Single pulse avalanche energy	77	mJ
T_J, T_{STG}	Storage Temperature Range	-55 to 175	°C
I_S	Diode Continuous Forward Current	$T_c=25^\circ\text{C}$ -45	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	$T_c=25^\circ\text{C}$ -180	A
I_D	Continuous Drain Current	$T_c=25^\circ\text{C}$ -45	A
P_D	Maximum Power Dissipation	$T_c=25^\circ\text{C}$ 30	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	55	°C/W

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MEAD45AP	PDFN3X3-8L	MEAD45AP	5,000	10,000	70,000	13"reel

Electrical Characteristics (TJ=25°C unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-30	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-30V, V _{GS} =0V	--	--	-1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1.0	-1.5	-2.5	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =-10V, I _D =-20A	--	8.0	12	mΩ
		V _{GS} =-4.5V, I _D =-10A	--	12	16	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	--	2850	--	pF
C _{OSS}	Output Capacitance		--	410	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	280	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DD} =-15V, I _D =-15A, V _{GS} =-10V	--	48	--	nC
Q _{gs}	Gate Source Charge		--	12	--	nC
Q _{gd}	Gate Drain Charge		--	14	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =-15V, I _D =-15A, V _{GS} =-10V, R _G =3Ω	--	15	--	nS
t _r	Turn-on Rise Time		--	11	--	nS
t _{d(off)}	Turn-Off Delay Time		--	45	--	nS
t _f	Turn-Off Fall Time		--	21	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	TJ=25°C, Is=-10A	--	--	-1.2	V

Typical Operating Characteristics

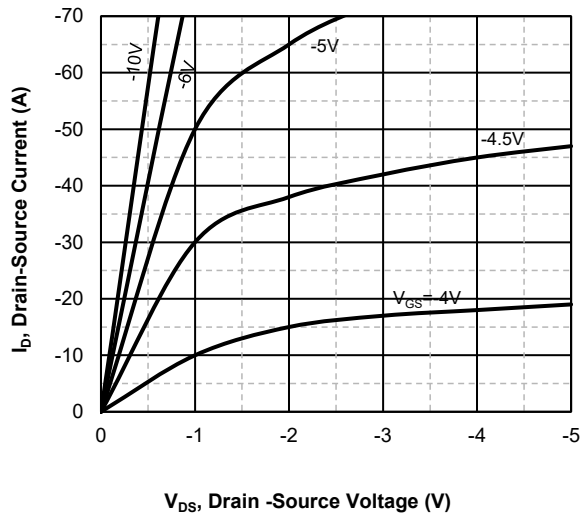


Fig1. Typical Output Characteristics

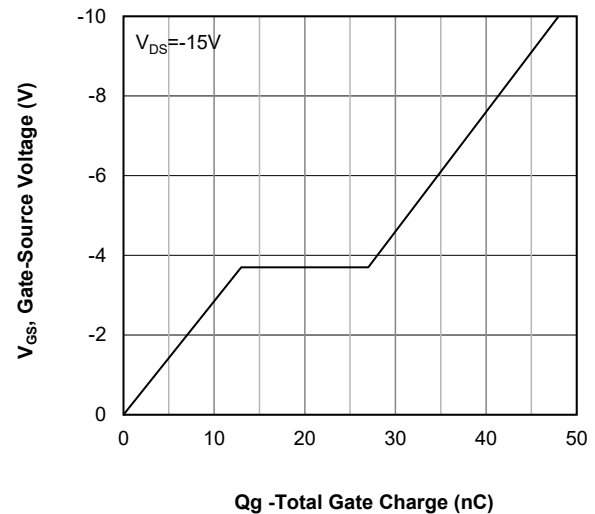


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

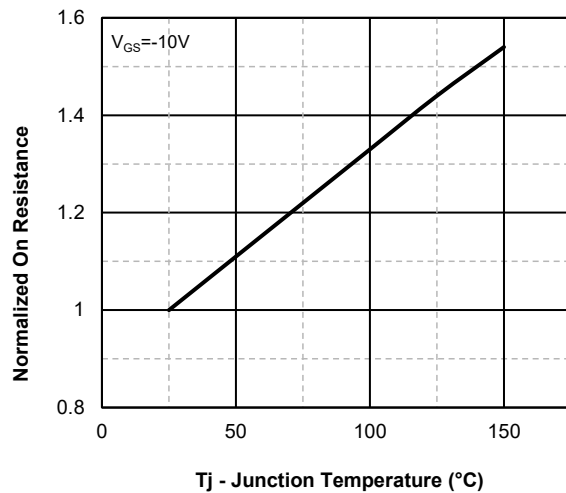


Fig3. Normalized On-Resistance Vs. Temperature

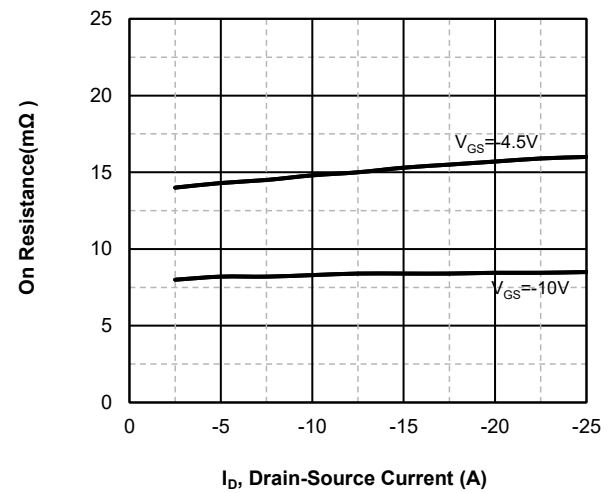


Fig4. On-Resistance Vs. Drain-Source Current

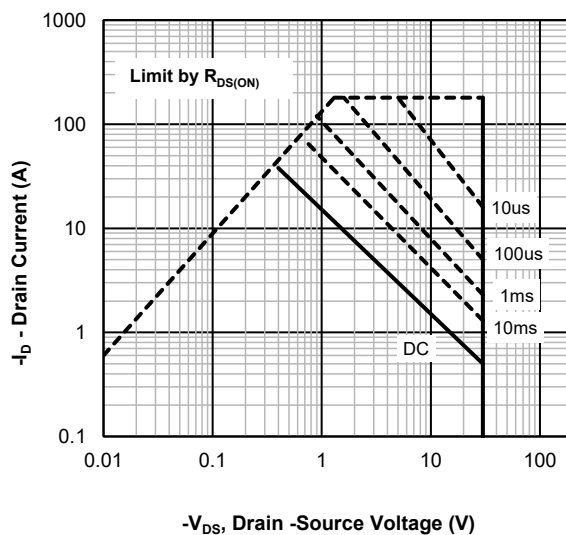


Fig5. Maximum Safe Operating Area

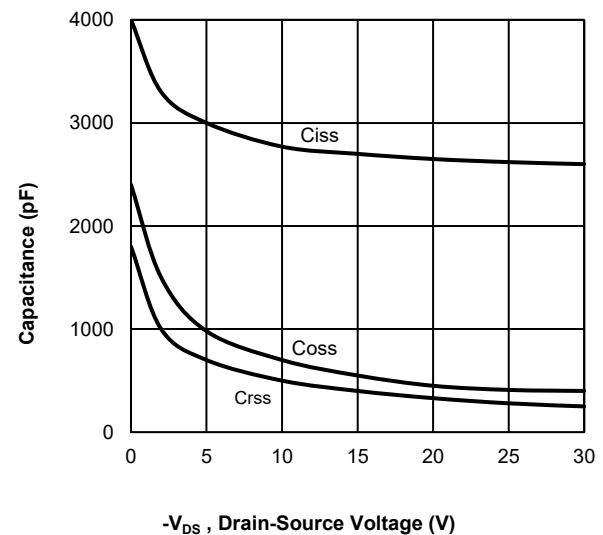
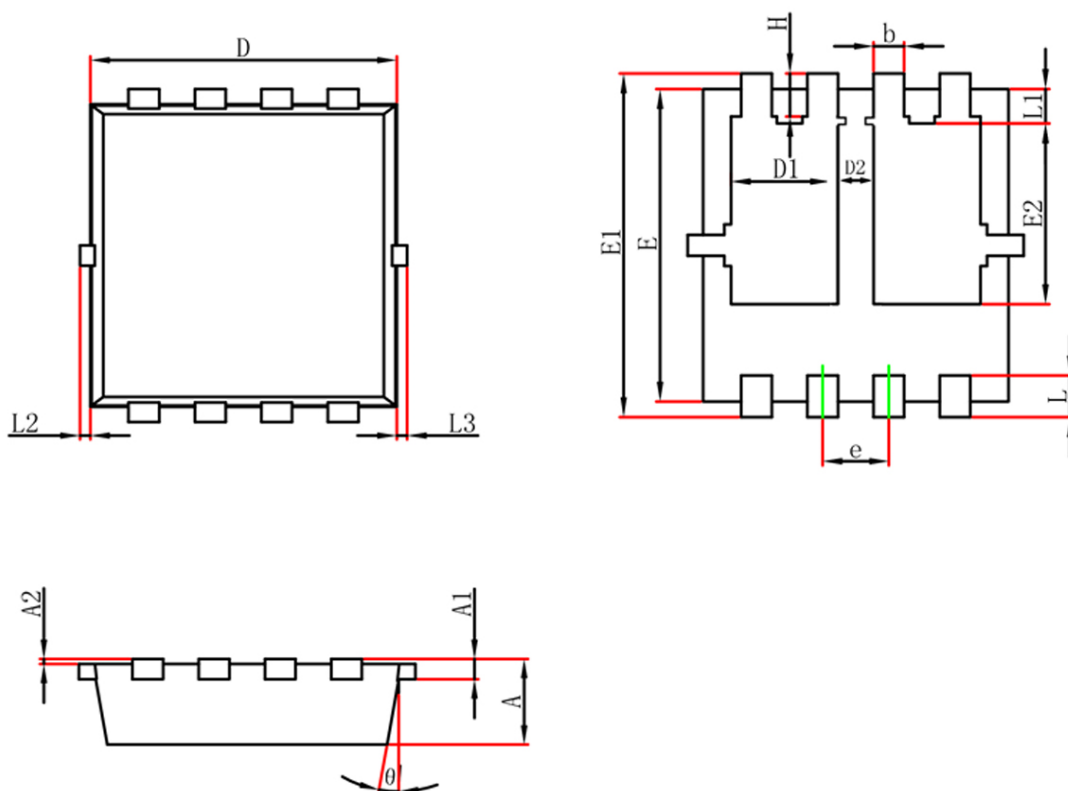


Fig6. Typical Capacitance Vs. Drain-Source Voltage

PDFN3X3-8L Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions in Inches	
	Min	Max	Min	Max
A	0.750	0.850	0.030	0.034
A1	0.152 REF.		0.006 REF.	
A2	0~0.05		0~0.002	
D	3.050	3.150	0.121	0.125
D1	0.985	1.085	0.039	0.043
D2	0.330	0.430	0.013	0.017
E	2.950	3.050	0.117	0.121
E1	3.250	3.350	0.129	0.132
E2	1.685	1.785	0.067	0.071
b	0.250	0.350	0.010	0.014
e	0.600	0.700	0.024	0.028
L	0.350	0.450	0.014	0.018
L1	0.280	0.380	0.011	0.015
L2	0~0.100		0~0.004	
L3	0~0.100		0~0.004	
H	0.350	0.450	0.014	0.018
θ	9°	13°	10°	12°